- ROM

Masked Rom, PROM, EPROM, EEPROM, Flash memory

-RAM

SRAM, DRAM

ROM (read-only memory)

= Galisma sirasinda sadece ok-nabilir.

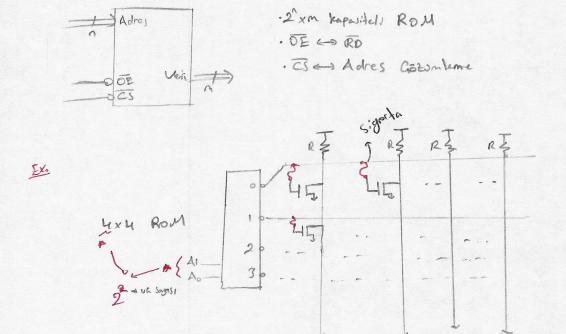
- * Non-Volatile: enerli kestleliginde veri kaybolmaz
- # 8086 reset vektorade ROM gerlesih

= Gesitler

- . Masked Rom: inslatta programlanir
- *PROM (programmable ROM): killance 1 kere programlayabilir
- · EPROM (erasable prom): operasyon svrasnda kapalı olan bir penceden uv Işıkla Silinebilir.
- · EE PROM (electrically Eprom): programlana valarindan silinnes: soglana
- · Flash Memory: bloblar halinde silme

*PROM: fuse Esigortal likk tek. kullant.

ROM Blok Dijagrami



D3

bo

* Sigortalaru yahılıp, korunmalı, proglama yapmamızı Sağları

- Sigorta yakılı => o

n korunyoral

01412

- · Volatile
- . Hith ohume, yatma
- . main memory

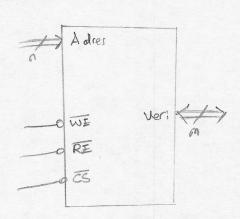
The opposite of random accept.

Traversing memory is required

= GesiHers

- SRAM (static) FF larle tosarlanming
- DRAM (dynamic) transitor ve kapasitor. [Bells aralihlarda deger ber gincellenir]

SRAM



2'xm kapasitel: SRAM

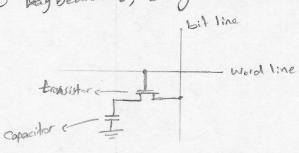
RE - RO

WE CO WR

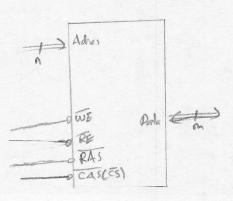
CS Co Adres Gazintene

DRAM

- · kapasite + trans : itor aifflerinden oluşır · futtige lotte deger belirli aralıklarla gencellenmek zorundadır
- . Her bir houresi SRAMIa gare entegrade 4 kat daha az der kaplar
 - . O bay bedilmer, 1 goncellermorse kaybedilir.



(1-bit DRAM Cell)



2 xm kapasiteli ORAM

RE 40 RD

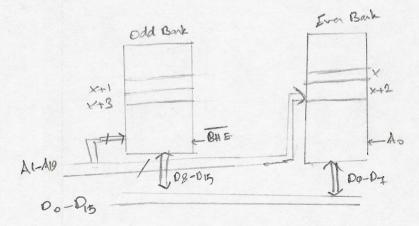
WE WE WR

RAS : cow select

CAS (CS) : column scheet

-20 un ile 2=1M hafita gots adreslarebilin

- Bir brim 8 bit.



" Tele adres 16-bit

Tek cycle'da olamaz. erekadresten 8-bit All'ea, aift adresten 8-bit Al'ye ayri ayrı cycle'larda aktorilir.

Es Separate bank decoder tele adresler ve cult adresler ich agri agri as uclam kullander



Seperate Bank Strobe Tek CS. Lajik bir devre ile BHE ve Ap WE VE RE Iam Kulanılır.

